NSN 5961-00-760-1952

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-760-1952 **Inclosure Material:** Metal **Overall Length:** 1.222 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 0.437 inches **Thread Size:** 0.190 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 200.0 breakover voltage, dc **Current Rating Per Characteristic:** 60.00 amperes forward current, average absolute **Power Rating Per Characteristic:** 500.0 milliwatts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 105.0 degrees celsius junction **Special Features:** Junction pattern arrangement: pnpn **Thread Series Designator: Terminal Type And Quantity:** 1 threaded stud and 2 tab, solder lug Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig:

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